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August 2014

FDPF045N10A

N-Channel PowerTrench[®] MOSFET 100 V, 67 A, 4.5 m Ω

Features

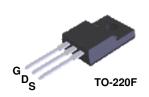
- $R_{DS(on)}$ = 3.7 m Ω (Typ.)@ V_{GS} = 10 V, I_D = 67 A
- · Fast Switching Speed
- Low Gate Charge, Q_G = 57 nC(Typ.)
- High Performance Trench Technology for Extremely Low $R_{\mbox{\footnotesize{DS}}(\mbox{\footnotesize{on}})}$
- · High Power and Current Handling Capability
- · RoHS Compliant

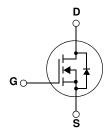
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor[®]'s advance PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- · Motor drives and Uninterruptible Power Supplies
- · Micro Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol		Parameter		FDPF045N10A	Unit	
V _{DSS}	Drain to Source Voltage			100	V	
V _{GSS}	Gate to Source Voltage		/	±20	V	
Dunin Course		- Continuous (T _C = 25°C)		67	A	
ID	Diam Current	- Continuous (T _C = 100°C)		47	^	
I _{DM}	Drain Current	- Pulsed	(Note 1)	268	Α	
E _{AS}	Single Pulsed Avalanche E	nergy	(Note 2)	637	mJ	
dv/dt	Peak Diode Recovery dv/d	t	(Note 3)	6.0	V/ns	
D	Dawer Dissipation	$(T_C = 25^{\circ}C)$		43	W	
P_{D}	Power Dissipation	- Derate above 25°C		0.29	W/°C	
T _J , T _{STG}	Operating and Storage Ten	nperature Range		-55 to +175	°C	
TL	Maximum Lead Temperatu	re for Soldering,1/8" from Case for 5 Se	econds	300	°C	

Thermal Characteristics

Symbol	Parameter FDPF045N10A		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	* C/ VV

Package Marking and Ordering Information

Device Marking	Device	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF045N10A	FDPF045N10A	TO-220F	Tube	-	-	50

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C	-	0.06	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	-	-	1	μА
IDSS	Zero Gate Voltage Drain Guirent	$V_{DS} = 80V, T_{C} = 150^{\circ}C$	-	-	500	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	2.0	-	4.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10V, I_D = 67A$	-	3.7	4.5	mΩ
g _{FS}	Forward Transconductance	$V_{DS} = 10V, I_{D} = 67A$	-	127	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 50V V 0V	-	3961	5270	рF
C _{oss}	Output Capacitance	$V_{DS} = 50V, V_{GS} = 0V$ f = 1MHz		925	1230	рF
C _{rss}	Reverse Transfer Capacitance	1 - 1101112	-	34	-	рF
C _{oss} (er)	Energy Releted Output Capacitance	$V_{DS} = 50V, V_{GS} = 0V$	-	1521	-	pF
Q _{g(tot)}	Total Gate Charge at 10V		-	57	74	nC
Q _{gs}	Gate to Source Gate Charge	$V_{GS} = 10V, V_{DS} = 50V$	-	17	-	nC
Q _{gs2}	Gate Charge Threshold to Plateau	I _D = 100A	-	8	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	13	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1MHz	-	1.9	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	23	56	ns
t _r		$V_{DD} = 50V, I_{D} = 100A$	-	26	62	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10V$, $R_{GEN} = 4.7\Omega$	-/	50	110	ns
t _f	Turn-Off Fall Time	(Note 4)	-	15	40	ns

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current			-	67	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	268	Α
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{SD} = 67A$	-	-	1.3	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0V, V_{DD} = 50V, I_{SD} = 100A$	-	75	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	-	120	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 3mH, I_{AS} = 20.6A, R_{G} = 25 $\Omega,$ Starting T_{J} = 25 $^{\circ}C$
- 3. $I_{SD} \leq 100 A, \ di/dt \leq 200 A/\mu s, \ V_{DD} \leq BV_{DSS}, \ Starting \ T_J = 25^{\circ}C$
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

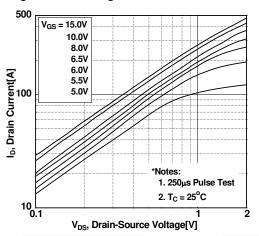


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

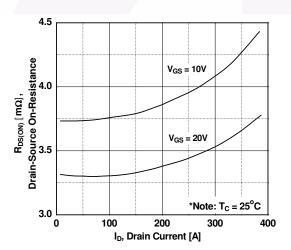


Figure 5. Capacitance Characteristics

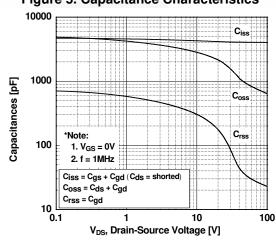


Figure 2. Transfer Characteristics

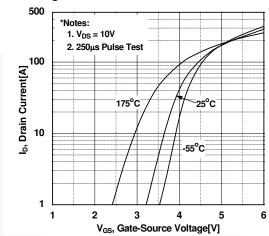


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

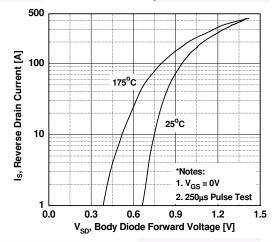
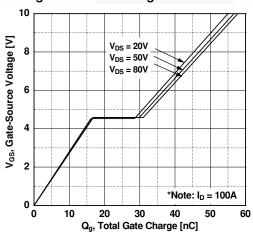


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

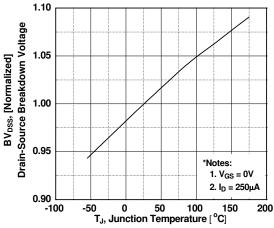


Figure 9. Maximum Safe Operating Area

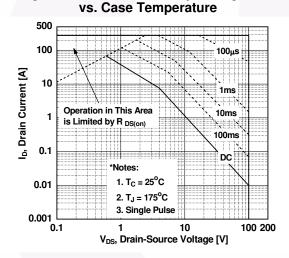


Figure 11. Eoss vs. Drain to Source Voltage

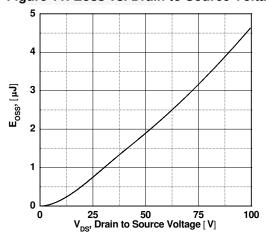


Figure 8. On-Resistance Variation vs. Temperature

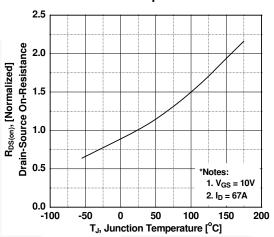
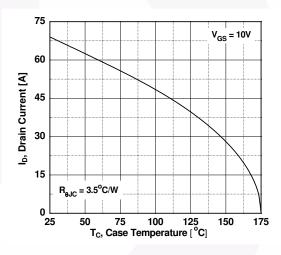
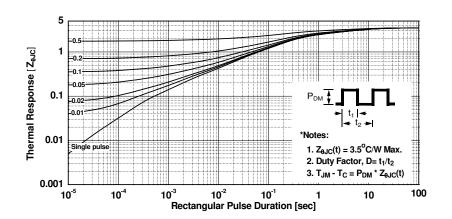


Figure 10. Maximum Drain Current



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



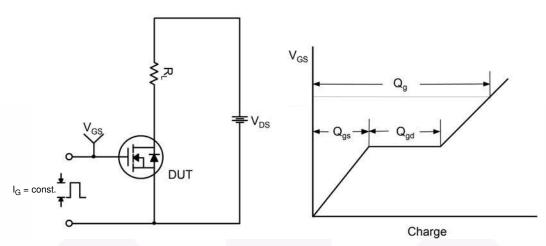


Figure 13. Gate Charge Test Circuit & Waveform

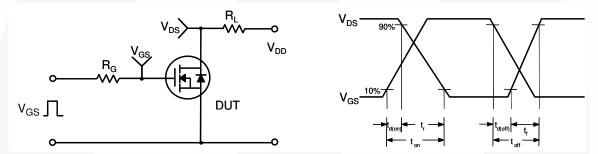


Figure 14. Resistive Switching Test Circuit & Waveforms

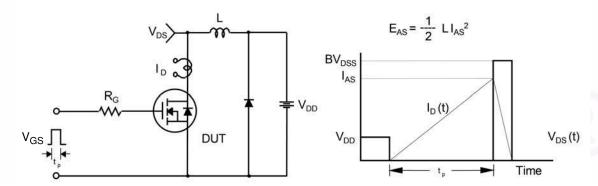


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

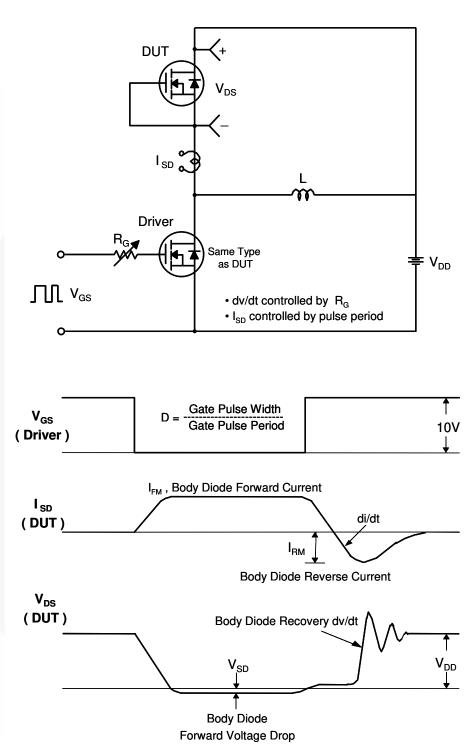


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

Mechanical Dimensions

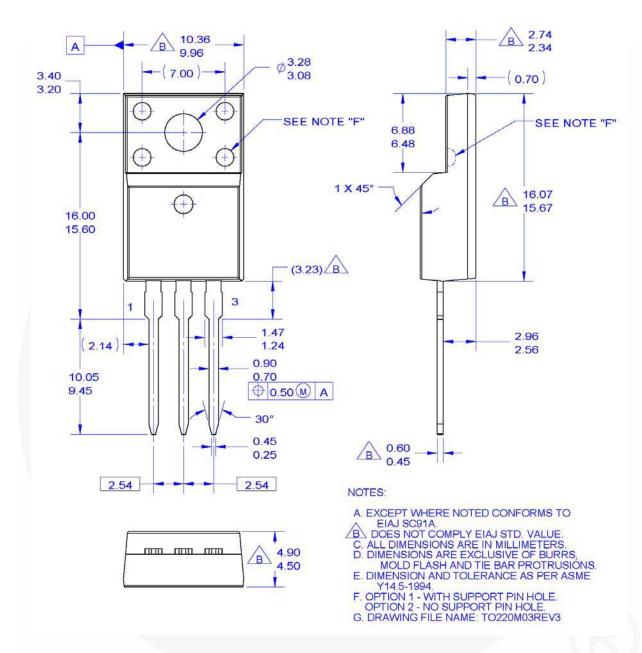


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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